BT137X-600F

4Q Triac

Rev.01 - 18 April 2018 | Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT186A (TO-220F) plastic package intended for use in general purpose bidirectional switching and phase control applications.

2. Features and benefits

- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Less sensitive gate for improved noise immunity
- Triggering in all four quadrants
- Isolated package

3. Applications

- General purpose motor control
- General purpose switching

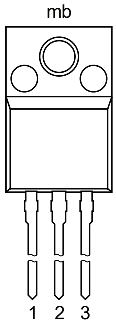
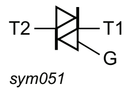
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Absolute maximum rating							
V_{DRM}	repetitive peak off-state voltage				600		V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 73$ °C; Fig. 1; Fig. 2; Fig. 3			8		A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5			65		A
Symbol	**Parameter**	**Conditions**		**Min**	**Typ**	**Max**	**Unit**
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12$ V; $I_T = 0.1$ A; T2+ G+; $T_j = 25$ °C; Fig. 7		-	5	25	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2+ G-; $T_j = 25$ °C; Fig. 7		-	8	25	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2- G-; $T_j = 25$ °C; Fig. 7		-	11	25	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2- G+; $T_j = 25$ °C; Fig. 7		-	30	70	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT137X-600F	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

7. Marking

Table 4. Marking codes

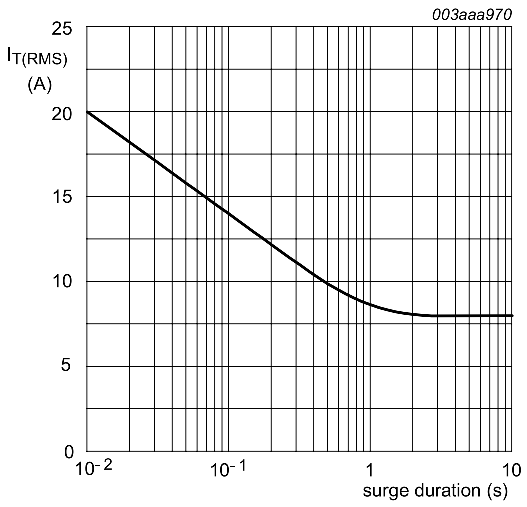
Type number	Marking codes
BT137X-600F	BT137X-600F

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 73$ °C; Fig 1; Fig 2; Fig 3	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig 4; Fig 5	65	A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms	71	A
I^2t	I^2t for fusing	$t_p = 10$ ms; SIN	21	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 50$ mA; T2+ G+	50	A/µs
		$I_G = 50$ mA; T2+ G-	50	A/µs
		$I_G = 50$ mA; T2- G-	50	A/µs
		$I_G = 140$ mA; T2- G+	140	A/µs
I_{GM}	peak gate current		2	A
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T_{stg}	storage temperature		-40 to 150	°C
T_j	junction temperature		125	°C



f = 50 Hz; T_h = 73 °C

Fig. 1. RMS on-state current as a function of surge duration; maximum values

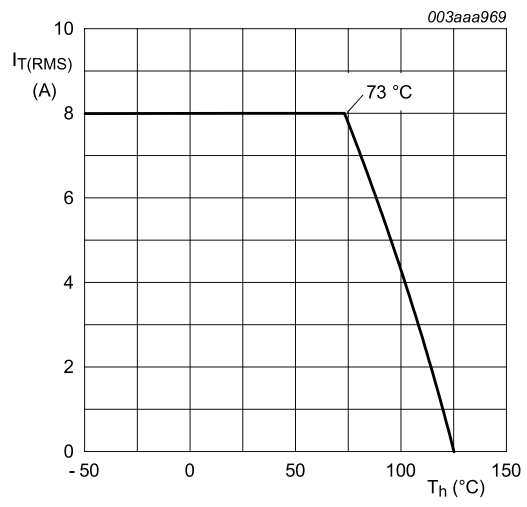
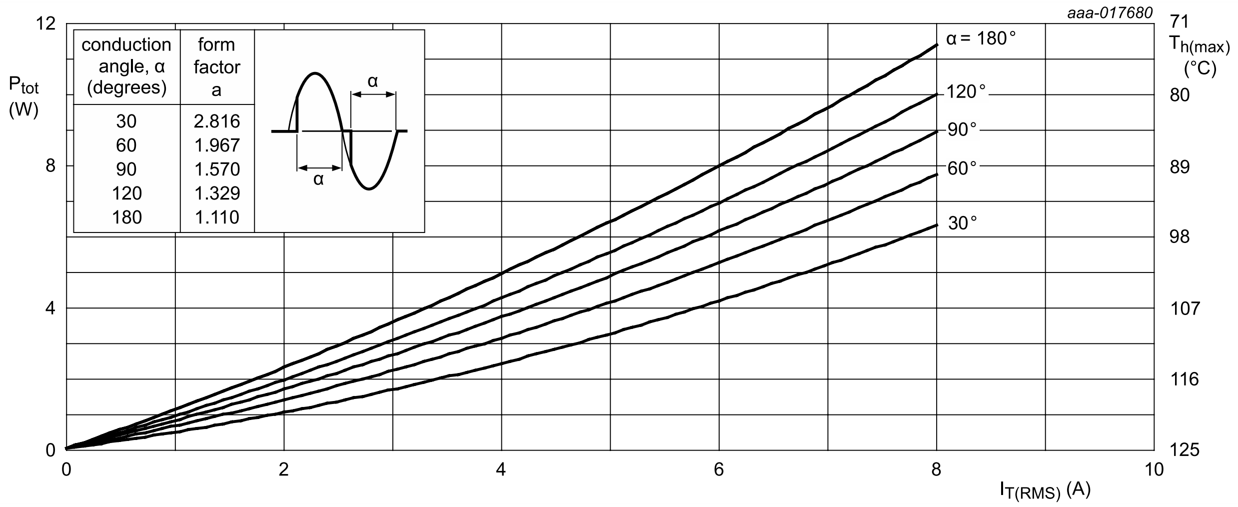


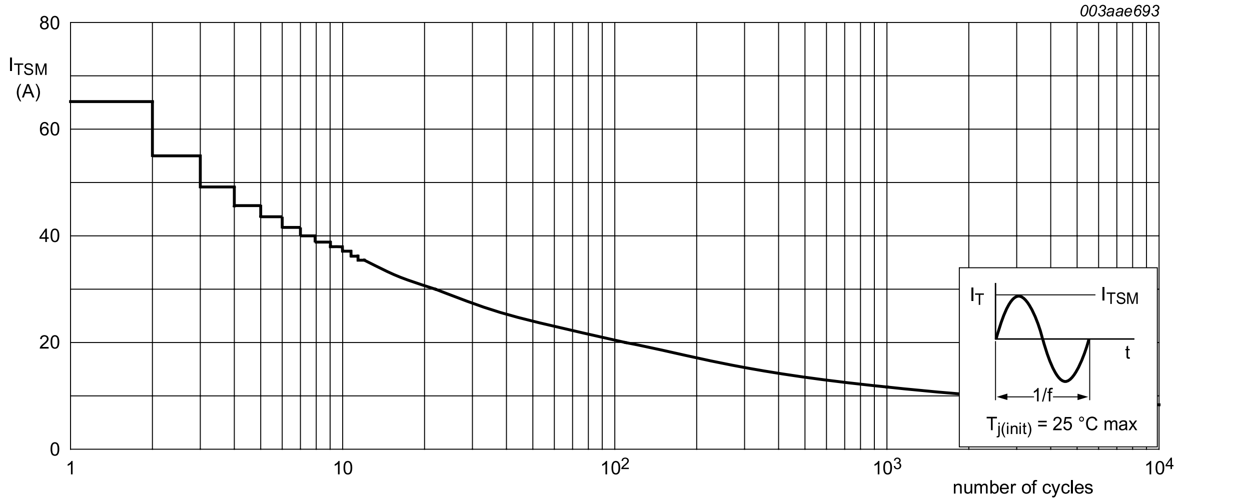
Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values



α = conduction angle

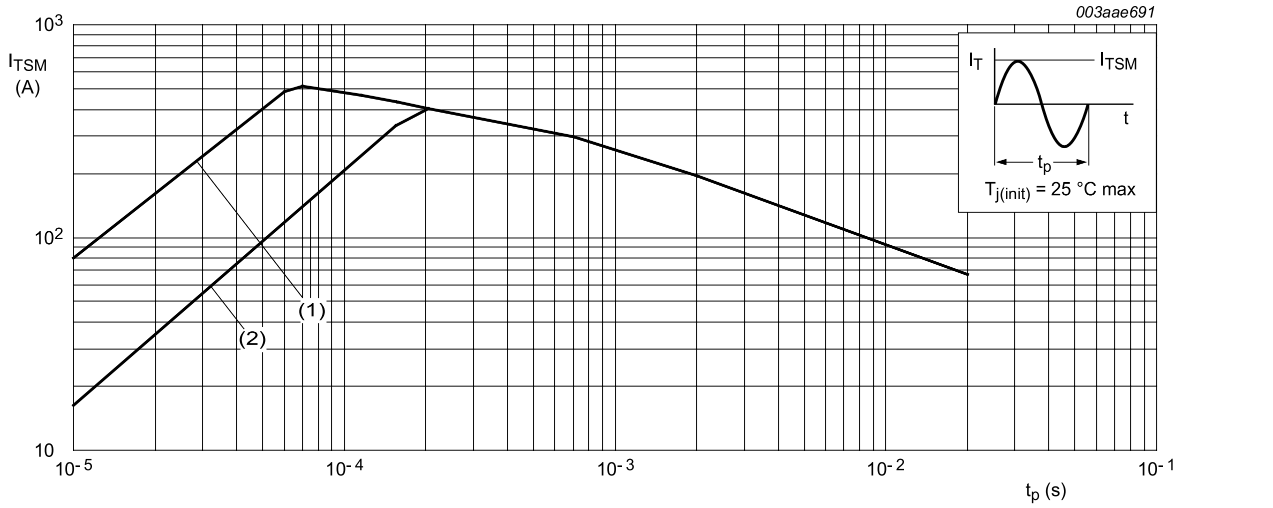
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



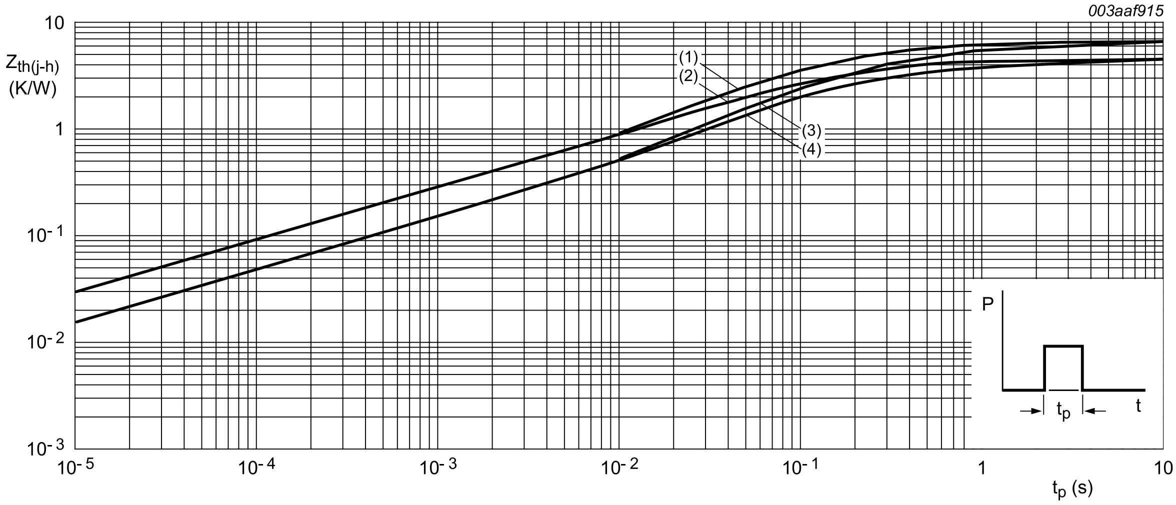
$t_p \leq 20$ ms
(1) dI_T/dt limit
(2) T2- G+ quadrant limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full or half cycle; with heatsink compound; Fig 6		-	-	4.5	K/W
		full or half cycle; without heatsink compound; Fig 6		-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	55	-	K/W



(1) Unidirectional (half cycle) without heatsink compound
(2) Unidirectional (half cycle) with heatsink compound
(3) Bidirectional (full cycle) without heatsink compound
(4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

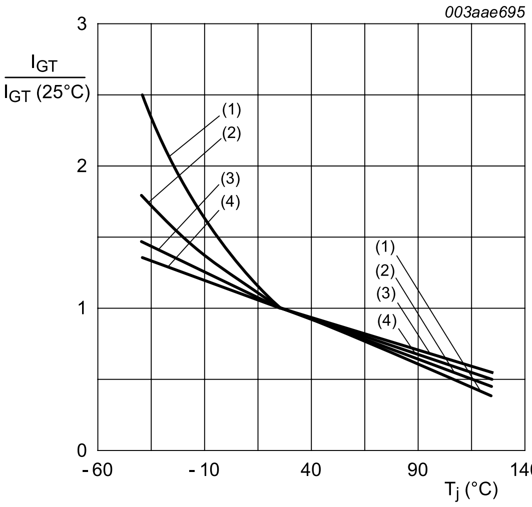
Table 7. Isolation characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; T_h = 25 °C		-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T_h = 25 °C		-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		-	5	25	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		-	8	25	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		-	11	25	mA
		V_D = 12 V; I_T = 0.1 A; T2- G+; T_j = 25 °C; Fig. 7		-	30	70	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 8		-	7	30	mA
		V_D = 12 V; I_G = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 8		-	16	45	mA
		V_D = 12 V; I_G = 0.1 A; T2- G-; T_j = 25 °C; Fig. 8		-	5	30	mA
		V_D = 12 V; I_G = 0.1 A; T2- G+; T_j = 25 °C; Fig. 8		-	7	45	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	5	20	mA
V_T	on-state voltage	I_T = 10 A; T_j = 25 °C; Fig. 10		-	1.3	1.65	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11		-	0.7	1	V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 °C; Fig. 11		0.25	0.4	-	V
I_D	off-state current	V_D = 600 V; T_j = 125 °C		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		50	250	-	V/µs
dV_{com}/dt	rate of change of commutating voltage	V_D = 400 V; T_j = 95 °C; dI_{com}/dt = 3.6 A/ms; I_T = 8 A		-	20	-	V/µs
t_{gt}	gate-controlled turn-on time	V_D = 600 V; I_{TM} = 12 A; I_G = 0.1 A; dI_G/dt = 5 A/µs		-	2	-	µs



(1) T2- G+
(2) T2- G-
(3) T2+ G-
(4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

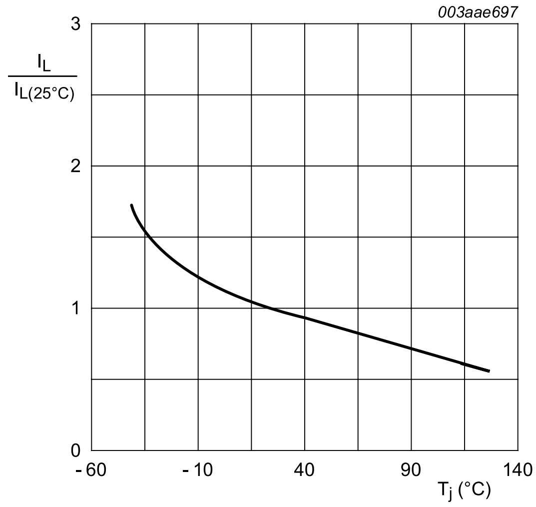


Fig. 8. Normalized latching current as a function of junction temperature

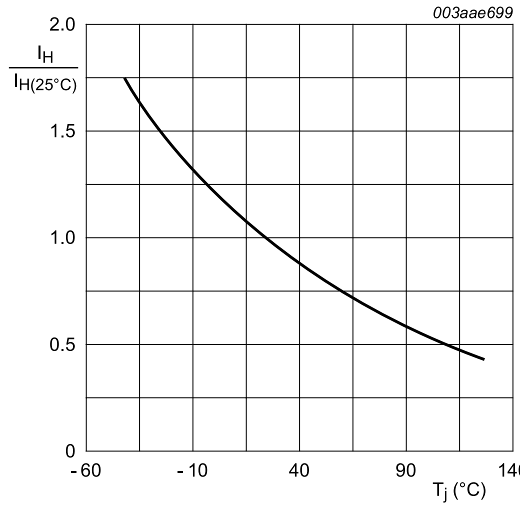
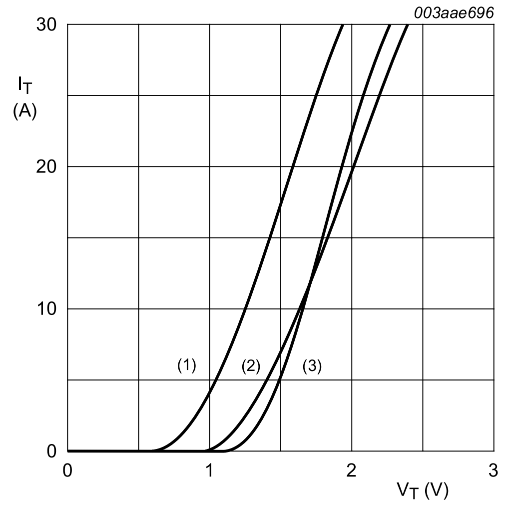


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 1.264 V; R_s = 0.038 Ω
(1) T_j = 125 °C; typical values
(2) T_j = 125 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

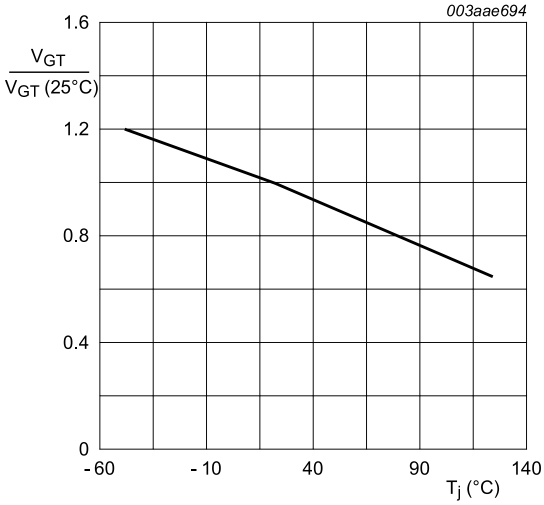
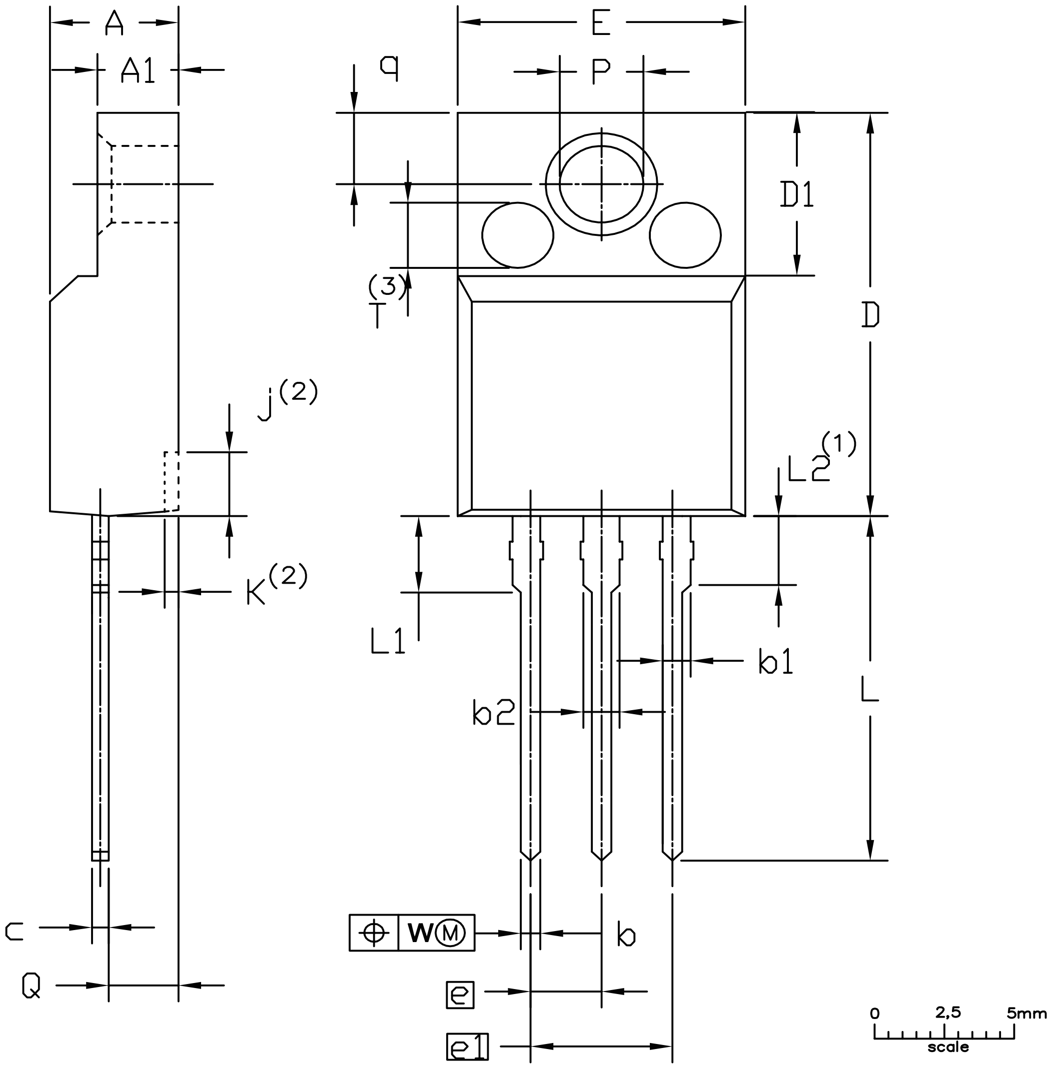


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" SOT186A



UNIT	A	A_1	b	b_1	b_2	c	D	D_1	E	e	e_1	j(2)	K(2)	L	L_1	L_2(1) max.	P	Q	q	W	T(3)
mm	4.6	2.9	0.9	1.1	1.4	0.7	15.8	6.5	10.3	2.54	5.08	2.7	0.6	14.4	3.30	3	3.2	2.6	3.0	0.4	2.5
	4.0	2.5	0.7	0.9	1.0	0.4	15.2	6.3	9.7			1.7	0.4	13.5	2.79		3.0	2.3	2.6		

Notes
1. Terminal dimensions within this zone are uncotrolled
2. Dot lines area designs may vary
3. Eject pin mark is for reference only

OUTLINE VERSION	REFERENCES IEC	REFERENCES JEDEC	REFERENCES JEITA		EUROPEAN PROJECTION	ISSUE DATE
SOT186A		3 LEADS TO220F				2013-11-14

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".
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14. Contents

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